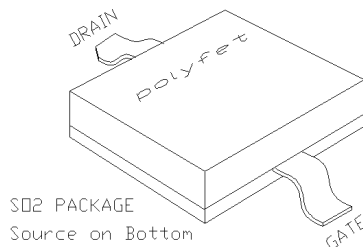




General Description

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others.

"Polyfet"TM process features low feedback and output capacitances, resulting in high F_T transistors with high input impedance and high efficiency.



SILICON GATE ENHANCEMENT MODE

RF POWER LDMOS TRANSISTOR

7.0 Watts Single Ended

Package Style S02

HIGH EFFICIENCY, LINEAR

HIGH GAIN, LOW NOISE

ROHS COMPLIANT

ABSOLUTE MAXIMUM RATINGS ($T = 25^{\circ}\text{C}$)

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
50 Watts	3.60°C/W	200°C	-65°C to 150°C	4.0 A	70 V	70 V	20 V

RF CHARACTERISTICS (7.0 WATTS OUTPUT)

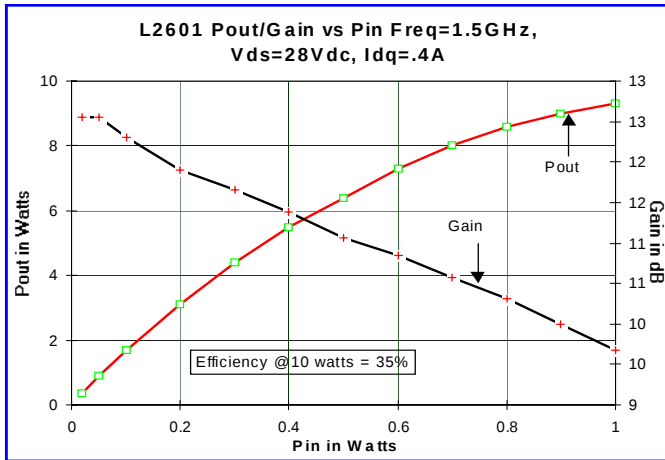
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	10			dB	$I_{dq} = 0.40\text{ A}$, $V_{ds} = 28.0\text{ V}$, $F = 1,500\text{ MHz}$
η	Drain Efficiency		35		%	$I_{dq} = 0.40\text{ A}$, $V_{ds} = 28.0\text{ V}$, $F = 1,500\text{ MHz}$
VSWR	Load Mismatch Tolerance			10:1	Relative	$I_{dq} = 0.40\text{ A}$, $V_{ds} = 28.0\text{ V}$, $F = 1,500\text{ MHz}$

ELECTRICAL CHARACTERISTICS (EACH SIDE)

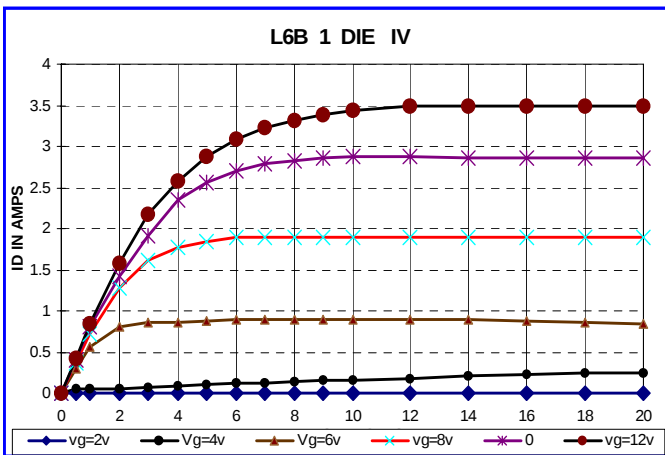
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	65			V	$I_{ds} = 0.10\text{ mA}$, $V_{gs} = 0\text{ V}$
Idss	Zero Bias Drain Current			1.0	mA	$V_{ds} = 28.0\text{ V}$, $V_{gs} = 0\text{ V}$
Igss	Gate Leakage Current			1	μA	$V_{ds} = 0\text{ V}$, $V_{gs} = 30\text{ V}$
Vgs	Gate Bias for Drain Current	2		5	V	$I_{ds} = 0.10\text{ A}$, $V_{gs} = V_{ds}$
gM	Forward Transconductance		0.5		Mho	$V_{ds} = 10\text{ V}$, $V_{gs} = 5\text{ V}$
Rdson	Saturation Resistance		0.90		Ohm	$V_{gs} = 20\text{ V}$, $I_{ds} = 2.50\text{ A}$
Idsat	Saturation Current		4.00		Amp	$V_{gs} = 20\text{ V}$, $V_{ds} = 10\text{ V}$
Ciss	Common Source Input Capacitance		16.0		pF	$V_{ds} = 28.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$
Crss	Common Source Feedback Capacitance		0.8		pF	$V_{ds} = 28.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$
Coss	Common Source Output Capacitance		13.0		pF	$V_{ds} = 28.0\text{ V}$, $V_{gs} = 0\text{ V}$, $F = 1\text{ MHz}$

L2601

POUT VS PIN GRAPH

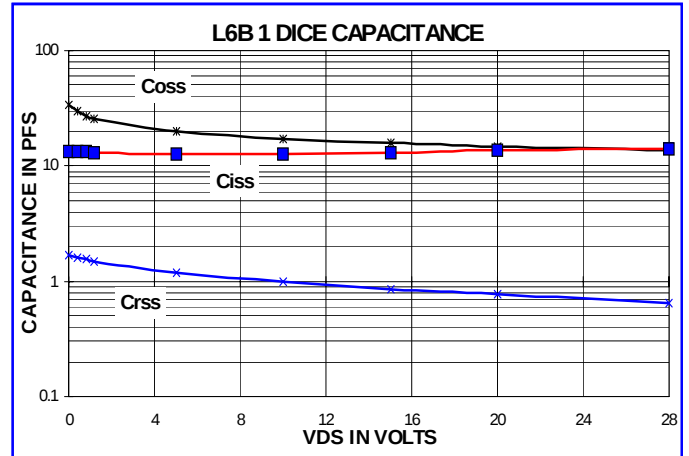


IV CURVE

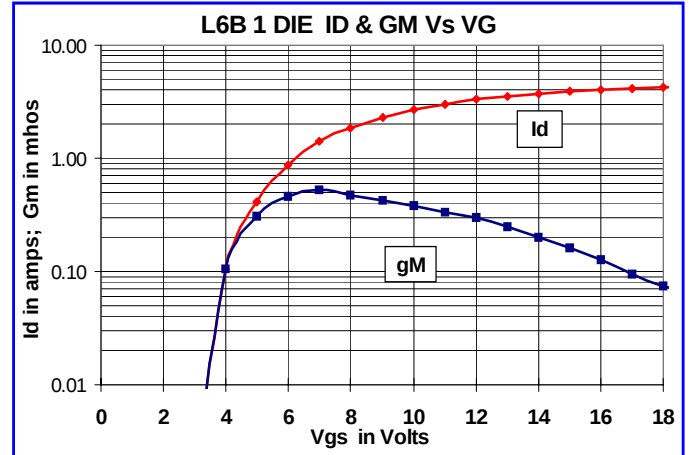


Zin Zout

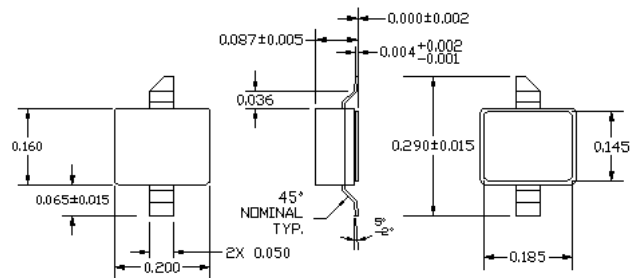
CAPACITANCE VS VOLTAGE



ID & GM VS VGS



PACKAGE DIMENSIONS IN INCHES



POLYFET S02 PACKAGE

Tolerance .XX +/-0.01 .XXX +/-0.005 inches

POLYFET RF DEVICES

REVISION 10/01/2007

1110 Avenida Acaso, Camarillo, Ca 93012 Tel:(805) 484-4210 FAX: (805) 484-3393 EMAIL:Sell@polyfet.com URL:www.polyfet.com